

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Chen, *et al.* Attorney Docket No.: TSM6283131RI
Serial No.: TBD Filed: Herewith
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Title: IN-SITU STRIP PROCESS FOR POLYSILICON ETCHING IN DEEP SUB-MICRON TECHNOLOGY

Mail Stop: REISSUE
Commissioner for Patents
P. O. Box 1450
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PRELIMINARY AMENDMENT

Dear Sir:

Prior to examination on the merits, Applicant respectfully submits the amendments and remarks set forth below.

In the claims:

Please add the following new claims:

20. (New) A method of forming a semiconductor device, the method comprising:
providing a semiconductor substrate with a conductive layer formed thereon;
providing a hard mask layer above said conductive layer;
providing a buffer layer above said hard mask layer;
providing a resist layer above said buffer layer;
patterning said resist layer to form a resist mask that exposes a part of said buffer layer;
and
patterning said conductive layer in a dry plasma etch chamber, said patterning